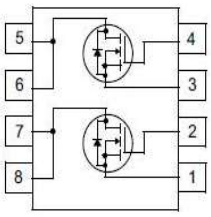
• General Description

It combines trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

• Product Summary



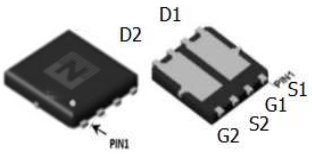
V_{DS}= 40V
$R_{DS(ON)}$ = 13mΩ
I_D= 19A

• Features

■AEC-Q101 Qualified
■Low $R_{DS(ON)}$ to minimize conductive loss
■Low Gate Charge for fast switching
■Low Thermal resistance

•Application

■BLDC Motor driver
■DC-DC
■Battery protection



DFN3*3

RoHS
REACH COMPLIANT
HF

•Ordering Information:

Part NO.	ZMDA68403M
Marking	68403
Packing Information	REEL TAPE
Basic ordering unit (pcs)	5000

•Absolute Maximum Ratings (T_C=25°C)

Parameter	Symbol	Conditions	Value	Unit
Drain-Source Voltage	V_{DS}		40	V
Gate-Source Voltage	V_{GS}		±20	V
Continuous Drain Current	I_D	T_C=25°C	19	A
	I_D	T_C=75°C	19	A
	I_D	T_C=100°C	17	A
Pulsed Drain Current ①	I_{DM}	Pulsed; tp < 10 μs; Tmb = 25°C	57	A
Total Power Dissipation	P_D	T_C=25°C	15	W
Total Power Dissipation	P_D	T_A=25°C	2.1	W
Operating Junction Temperature	T_J		-55 to +150	°C
Storage Temperature	T_{STG}		150	°C
Single Pulse Avalanche Energy	E_{AS}	L=0.1mH, V_{GS}=10V, Rg=25Ω,	24	mJ
		L=0.5mH, V_{GS}=10V, Rg=25Ω,	45.6	mJ
ESD Level (HBM)	CLASS 1C			

●Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}		-	8.4	°C/W
Thermal resistance, junction-ambient	R_{thJA}②		-	60	°C/W
Soldering temperature	T_{sold}		-	260	°C

●Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS} =0V, I_D =250uA	40			V
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} =V_{DS}, I_D =250uA	1.3	1.7	2.5	V
Drain-Source Leakage Current	I_{DSS}	V_{GS}=0V, V_{DS}= 40V			1	uA
Gate- Source Leakage Current	I_{GSS}	V_{GS}=±20V, V_{DS} =0V			100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D= 8A		13	18	mΩ
Diode Forward Voltage	V_{FSD}	V_{GS} =0V, I_{SD} = 8A			1.3	V

●Dynamic characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Input capacitance	Ciss	f = 1MHz, V_{DS}=25V	-	1190	-	pF
Output capacitance	Coss		-	52	-	
Reverse transfer capacitance	Crss		-	29	-	
Gate Risistance	Rg	f = 1MHz	-	2		Ω
Total gate charge	Qg	V_{DD} = 15V，I_D = 20A，V_{GS} = 10V	-	20	-	nC
Gate - Source charge	Qgs		-	3.3	-	
Gate - Drain charge	Qgd		-	3.6	-	
Turn-ON Delay time	$t_{D(on)}$	V_{GS}=10V,V_{DS}=15V，R_G =3.3Ω,I_D =20A	-	19	-	ns
Turn-ON Rise time	t_r		-	45	-	ns
Turn-Off Delay time	$t_{D(off)}$		-	46	-	ns
Turn-Off Fall time	t_f		-	42	-	ns
Reverse Recovery Time	t_{RR}	V_{DD}=20V,dI_S/dt = 100A/us,I_S=50A	-	21	-	ns
Reverse Recovery Charge	Q_{RR}		-	16	-	nC

Fig.1 Gate-Charge Characteristics

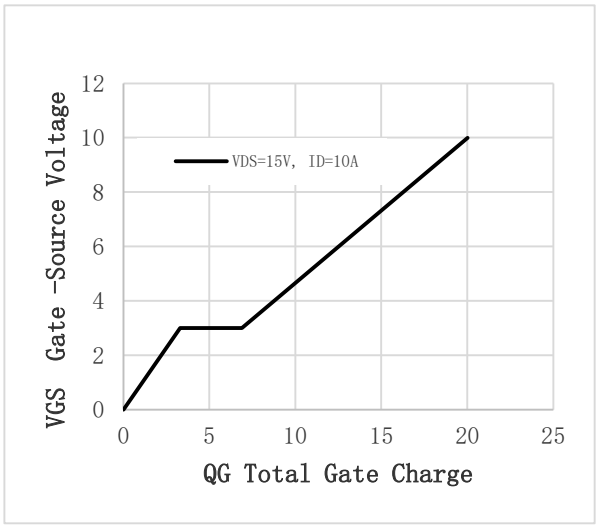


Fig.2 Capacitance Characteristics

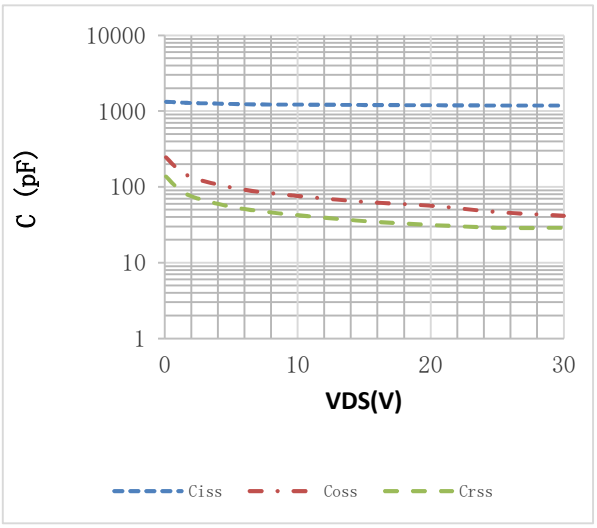


Fig.3 Power Dissipation

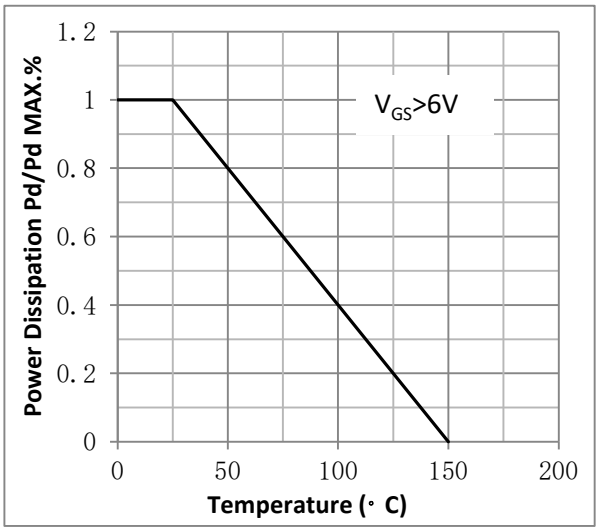


Fig.4 Typical output Characteristics

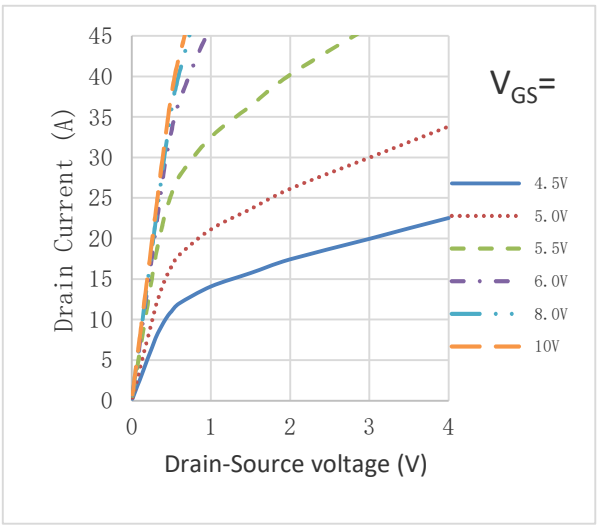


Fig.5 Threshold Voltage V.S Junction Temperature

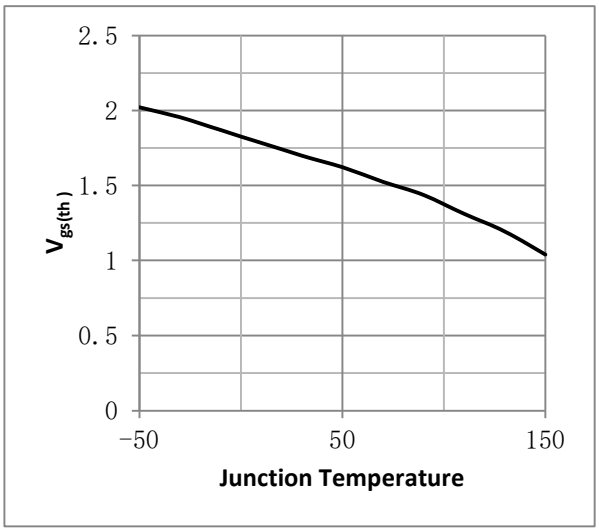


Fig.6 Resistance V.S Drain Current

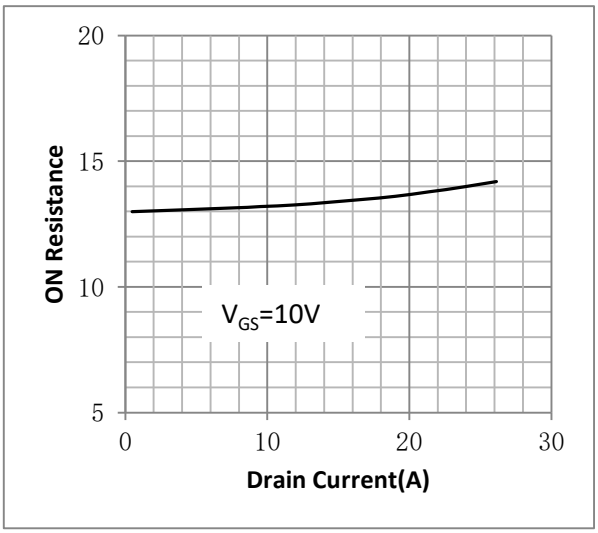


Fig.7 On-Resistance VS Gate Source Voltage

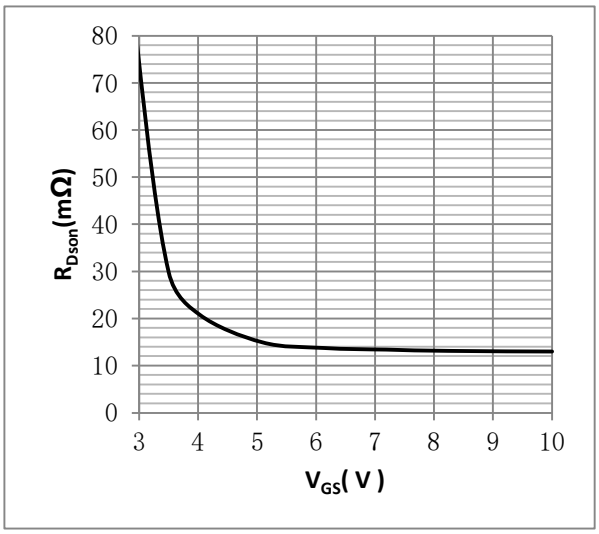


Fig.8 On-Resistance V.S Junction Temperature

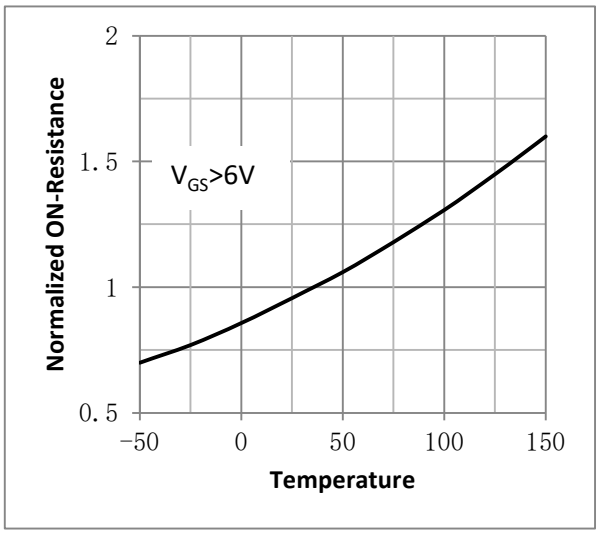


Figure 9. Diode Forward Voltage vs. Current

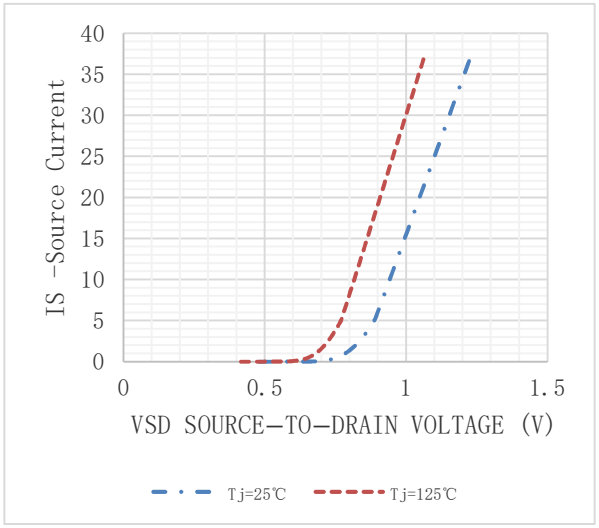


Figure 10. Transfer Characteristics

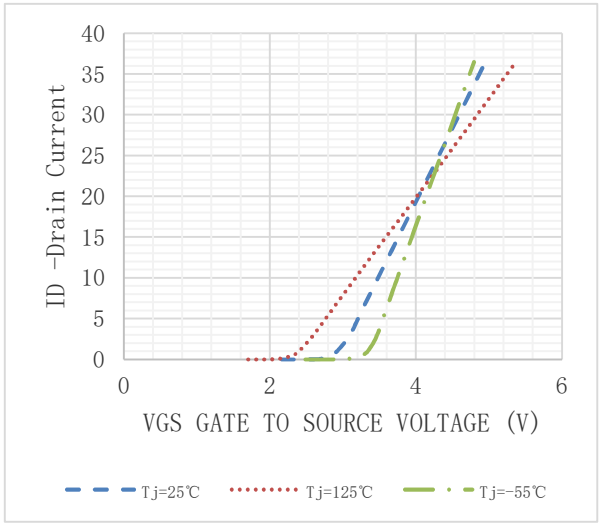


Fig.11 Maximum Safe Operating Area

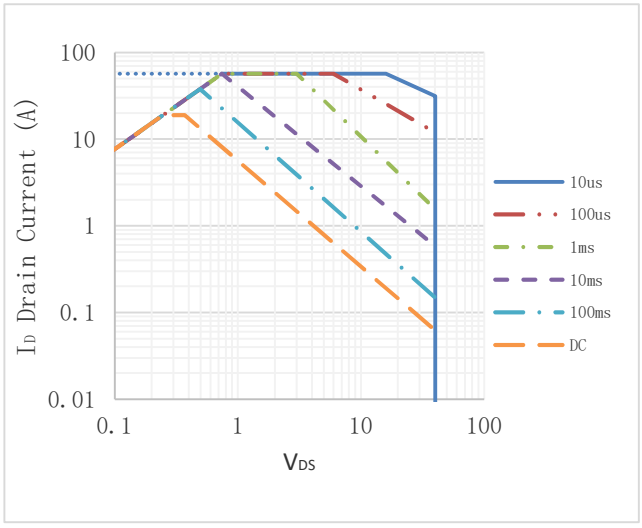
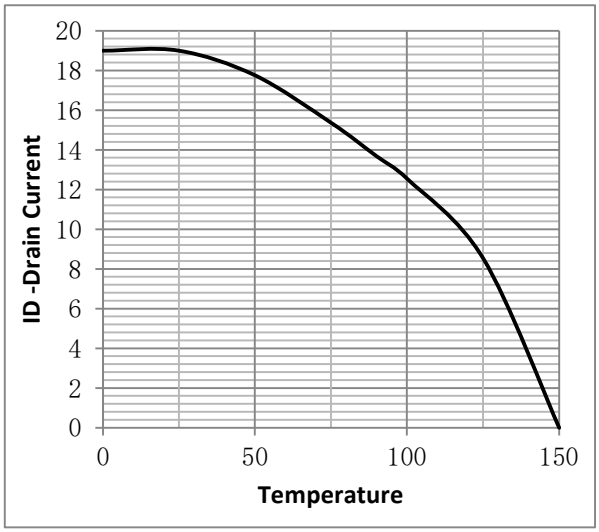
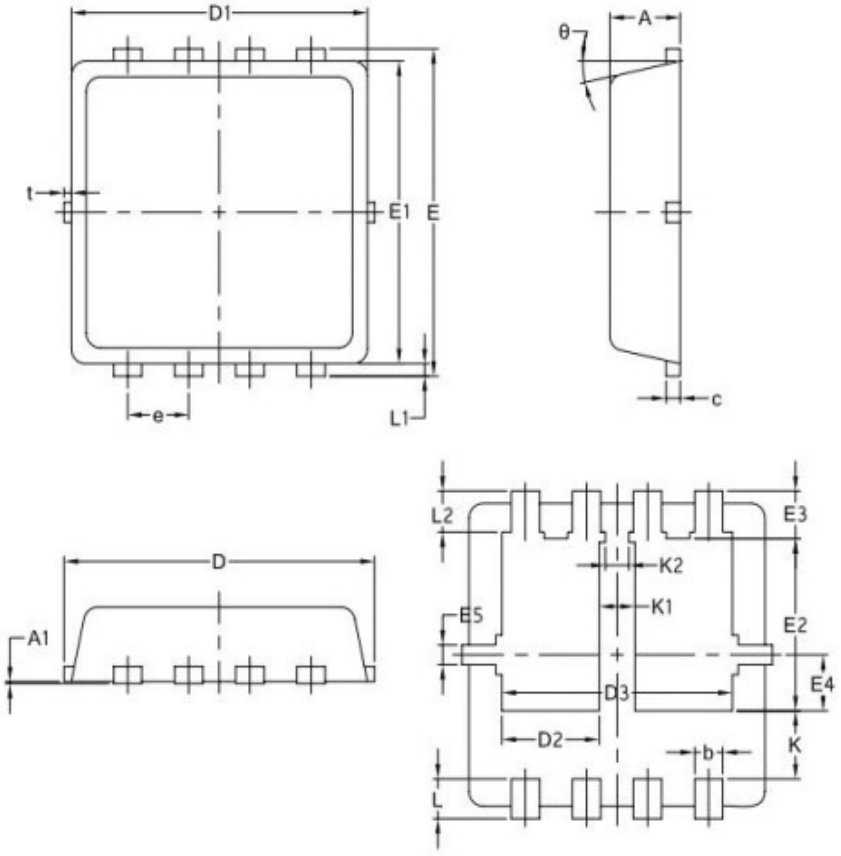


Fig.12 ID vs. Junction Temperature



●DFN3*3 Package Outline



SYMBOL	COMMON		
	MM		
	MIN	NOM	MAX
A	0.70	0.75	0.85
A1	/	/	0.05
b	0.25	0.30	0.39
c	0.14	0.152	0.20
D	3.20	3.30	3.45
D1	3.05	3.15	3.25
D2	0.84	1.04	1.24
D3	2.30	2.45	2.60
E	3.20	3.30	3.40
E1	2.95	3.05	3.15
E2	1.60	1.74	1.90
E3	0.28	0.48	0.65
E4	0.37	0.57	0.77
E5	0.10	0.20	0.30
e	0.60	0.65	0.70
K	0.50	0.69	0.80
K1	0.30	0.38	0.53
K2	0.15	0.25	0.35
L	0.30	0.40	0.50
L1	0.06	0.125	0.20
L2	0.27	0.42	0.57
t	0	0.075	0.13
θ	10°	12°	14°

Note:

① Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%, Accumulation time ≤50 hours; For DC， the following test conditions can be passed: VGS=+15V/-5V, Tj=150℃, t=1000 hours；

② Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate；

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Revision History

Version	Date	Change
A	2021.7.5	New
B	2021.12.6	Correct TJ
C	2022.6.12	Use new version.
D	2023.7.12	Correct Id